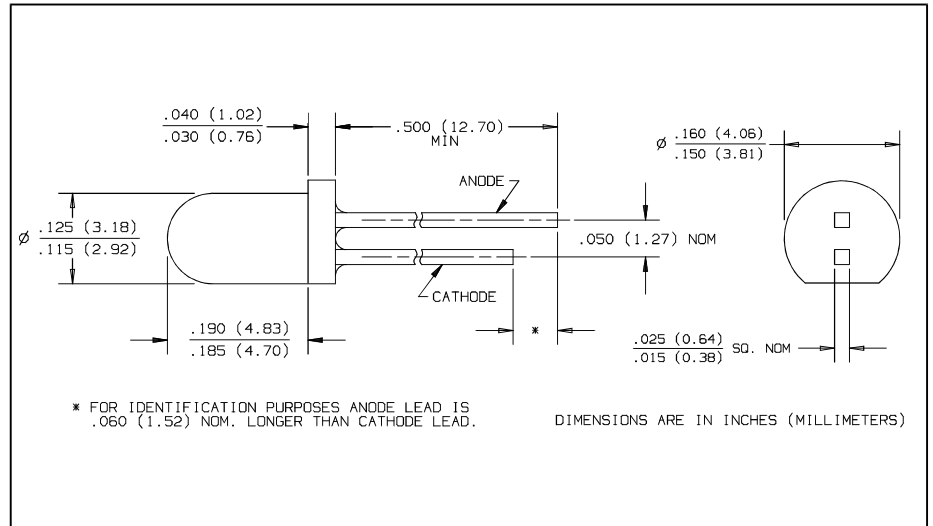


# PIN Silicon Photodiode Type OP905



## Features

- Narrow receiving angle
- Linear response vs. irradiance
- Fast switching time
- T-1 package style
- Small package ideal for space limited applications

## Description

The OP905 device consists of a PIN silicon photodiode molded in a clear epoxy package which allows spectral response from visible to infrared light wavelengths. The narrow receiving angle provides excellent on-axis coupling. These devices are 100% production tested using infrared light for close correlation with Optek's GaAs and GaAlAs emitters.

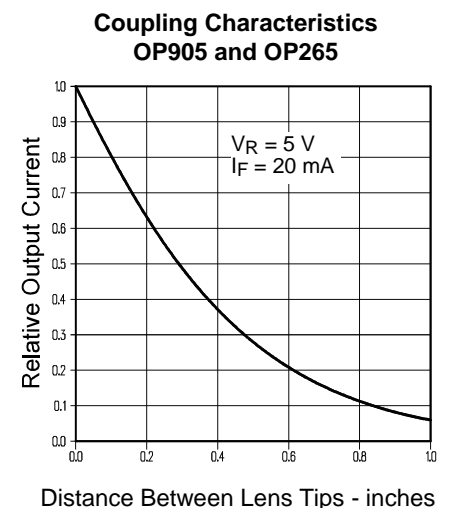
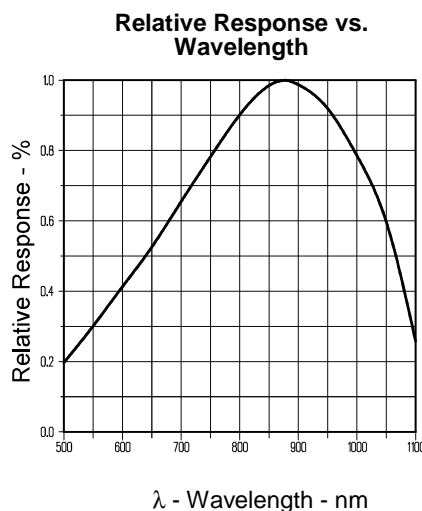
## Absolute Maximum Ratings ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

|  |   |
|--|---|
| Reverse Breakdown Voltage  | 60 V  |
| Storage and Operating Temperature Range  | $-40^\circ\text{C}$ to $+100^\circ\text{C}$ |
| Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 sec. with soldering iron] | $260^\circ\text{C}^{(1)}$                   |
| Power Dissipation  | 100 mW <sup>(2)</sup>                       |

### Notes:

- (1) RMA flux is recommended. Duration can be extended to 10 sec. max. when flow soldering. Max. 20 grams force may be applied to leads when soldering.
- (2) Derate linearly  $1.67\text{ mW}/^\circ\text{C}$  above  $25^\circ\text{C}$ .
- (3) Light source is an unfiltered GaAs LED with a peak emission wavelength of 935nm and a radiometric intensity level which varies less than 10% over the entire lens surface of the photodiode being tested.
- (4) To calculate typical dark current in nA, use the formula  $I_D = 10^{(0.042 T_A - 1.5)}$  where  $T_A$  is ambient temperature in  $^\circ\text{C}$ .

## Typical Performance Curves



# Type OP905

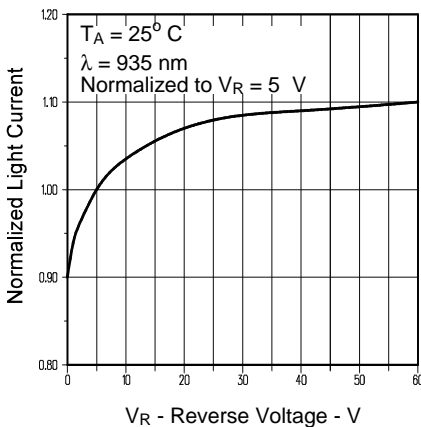
Electrical Characteristics ( $T_A = 25^\circ\text{C}$  unless otherwise noted)

| SYMBOL     | PARAMETER                 | MIN | TYP | MAX | UNITS         | TEST CONDITIONS  |
|------------|---------------------------|-----|-----|-----|---------------|--|
| $I_L$      | Reverse Light Current     | 14  |     | 32  | $\mu\text{A}$ | $V_R = 5\text{ V}$ , $E_e = 0.50\text{ mW/cm}^2$ <sup>(3)</sup>      |
| $I_D$      | Reverse Dark Current      |     | 1   | 60  | nA            | $V_R = 30\text{ V}$ , $E_e = 0$                                      |
| $V_{(BR)}$ | Reverse Breakdown Voltage | 60  |     |     | V             | $I_R = 100\ \mu\text{A}$   |
| $V_F$      | Forward Voltage           |     |     | 1.2 | V             | $I_F = 1\text{ mA}$  |
| $C_T$      | Total Capacitance         |     | 4   |     | pF            | $V_R = 20\text{ V}$ , $E_e = 0$ , $f = 1.0\text{ MHz}$               |
| $t_r, t_f$ | Rise Time, Fall Time      |     | 5   |     | ns            | $V_R = 20\text{ V}$ , $\lambda = 850\text{ nm}$ , $R_L = 50\ \Omega$ |

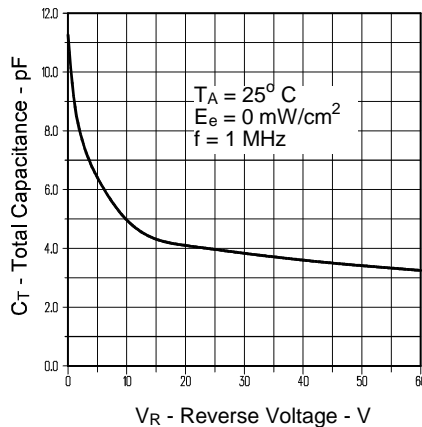
## Typical Performance Curves

PHOTOSENSORS

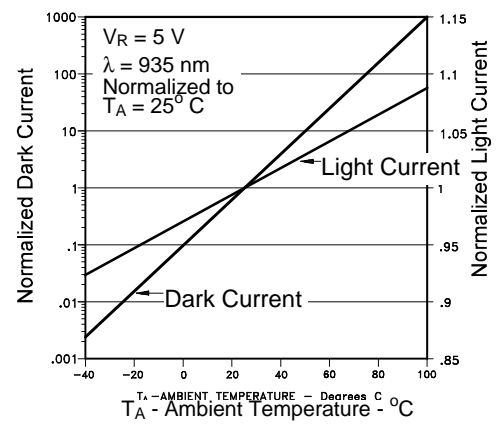
Normalized Light Current vs Reverse Voltage



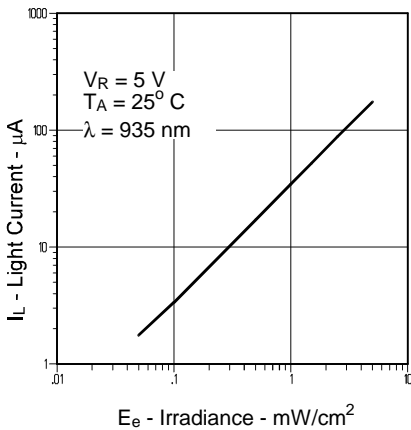
Total Capacitance vs Reverse Voltage



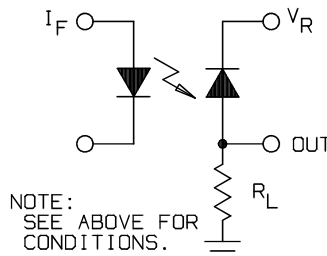
Normalized Light and Dark Current vs Ambient Temperature



Light Current vs. Irradiance



Switching Time Test Circuit



Light Current vs. Angular Displacement

